

## LIST OF THE CLAIMS

1-7. (Canceled)

8. (Currently amended) An apparatus for cleaning semiconductor substrates, comprising:

a chamber having a cleaning room in which the semiconductor substrates are cleaned and a drying room, disposed over the cleaning room, in which the semiconductor substrates are dried;

a supporter disposed in the chamber that supports the semiconductor substrates;

a supply pipe installed at an upper portion of the drying room that supplies a drying fluid comprising a gas onto the substrate; and

a separation plate which is movable to separate the cleaning room and the drying room or to place the cleaning room and the drying room in communication with one another, the separation plate having an exhaust path of the drying fluid therein,

wherein the exhaust path of the drying fluid passes the drying fluid comprising the gas from the drying room into the cleaning room,

wherein a plurality of first openings are formed in a top side of the separation plate and a plurality of second openings are formed in a bottom side of the separation plate, and wherein each of the exhaust path connects one of the plurality of the first openings and one of the plurality of the second openings ~~and is formed perpendicular to the separation plate.~~

9. (Original) The apparatus of claim 8, wherein the supply pipe comprises:

a first supply pipe for supplying alcohol vapor into the drying room; and

a second supply pipe for supplying a heated dry gas into the drying room.

10. (Original) The apparatus of claim 9, further comprising a cleaning solution supply pipe disposed in the cleaning room that injects the cleaning solution into the cleaning room, wherein the cleaning room further comprises:

an inner bath where the supporter is disposed; and

an outer bath disposed to surround the upper outer periphery of the inner bath, wherein the cleaning solution overflowing from the inner bath flows into the outer bath, and a drain port is formed at the bottom of the outer bath.

11. (Original) The apparatus of claim 10, wherein an exhaust port is formed at one side of the outer bath, and the drying fluid flowing into the cleaning room along the exhaust path of the separation plate is exhausted to the outside through the exhaust port.

12. (Original) The apparatus of claim 10, wherein the separation plate further comprises a separation plate moving part having a connecting rod fixedly connected to the separation plate and a driving part for horizontally moving the connecting rod.

13. (Original) The apparatus of claim 8, wherein the exhaust path comprises at least one hole or slit formed in the separation plate.

14. (Original) The apparatus of claim 13, wherein the at least one hole or slit comprises a plurality of holes and slits, and the plurality of holes or slits are formed in the separation plate, and sizes of the holes or widths of the slits differ according to their positions.

15. (Original) The apparatus of claim 13, wherein the at least one hole or slit comprises a plurality of holes or slits, and the plurality of holes or slits are formed in at

least one row at the central portion of the separation plate.

16. (Original) The apparatus of claim 15, wherein spaces between adjacent holes differ according to their forming positions.

17. (Original) The apparatus of claim 13, wherein the semiconductor substrates are placed in a row, and the row direction is vertical to processing surfaces of the semiconductor substrates.

18. (Currently amended) An apparatus for cleaning semiconductor substrates, comprising:

a chamber having a drying room in which the semiconductor substrates are dried;

a supply pipe installed in the drying room that supplies a drying fluid comprising a gas onto the semiconductor substrates;

a separation plate constituting a bottom of the drying room; and

a cleaning room disposed below the drying room and separated from the drying room by the separation plate;

wherein an exhaust path is formed at a central portion of the separation plate, and wherein the drying fluid[[s]] comprising the gas supplied onto the substrate ~~are is~~ exhausted from the drying room through the exhaust path and the exhausted drying fluid[[s]] ~~are is~~ passed into the cleaning room,

wherein a plurality of first openings are formed in a top side of the separation plate and a plurality of second openings are formed in a bottom side of the separation plate, and wherein each of the exhaust path connects one of the plurality of the first openings and one of the plurality of the second openings ~~and is formed perpendicular to the separation plate.~~

19. (Previously presented) The apparatus of claim 18, wherein the separation plate is movably disposed.

20. (Currently amended) An apparatus for cleaning semiconductor substrates, comprising:

a chamber comprising:

a cleaning room in which the semiconductor substrates are cleaned; and

a drying room, disposed over the cleaning room, in which the semiconductor substrates are dried by a drying fluid comprising a gas; and

a separation plate having an exhaust path of the drying fluid, wherein the separation plate that is movable between an open position in which the cleaning room is in communication with the drying room and a closed position in which the cleaning room is separated from the drying room thereby having a limited communication through the exhaust path.

wherein the exhaust path of the separation plate has an exhaust path of drying fluid therein, and the exhaust path of the drying fluid passes the drying fluid comprising the gas from the drying room into the cleaning room,

wherein a plurality of first openings are formed in a top side of the separation plate and a plurality of second openings are formed in a bottom side of the separation plate, and wherein each of the exhaust path connects one of the plurality of the first openings and one of the plurality of the second openings ~~and is formed perpendicular to the separation plate.~~

21. (Original) The apparatus of claim 20, further comprising:

a supporter disposed in the chamber that supports the semiconductor substrates.

22. (Previously presented) The apparatus of claim 21, further comprising:

a supply pipe installed in the drying room that supplies the drying fluid onto the semiconductor substrates.

23. (Original) The apparatus of claim 20, wherein the separation plate further comprises a separation plate moving part having a connecting rod fixedly connected to the separation plate and a driving part for horizontally moving the connecting rod.

24. (Original) The apparatus of claim 22, wherein the supply pipe comprises:  
a first supply pipe for supplying alcohol vapor into the drying room; and  
a second supply pipe for supplying a heated dry gas into the drying room.

25. (Original) The apparatus of claim 22, further comprising a cleaning solution supply pipe disposed in the cleaning room that injects the cleaning solution into the cleaning room, wherein the cleaning room further comprises:

an inner bath where the supporter is disposed; and

an outer bath disposed to surround the upper outer periphery of the inner bath, wherein the cleaning solution overflowing from the inner bath flows into the outer bath, and a drain port is formed at the bottom of the outer bath.

26. (Original) The apparatus of claim 25, wherein an exhaust port is formed at one side of the outer bath, and the drying fluid flowing into the cleaning room along the exhaust path of the separation plate is exhausted to the outside through the exhaust port.

27. (New) The apparatus of claim 8, wherein the gas comprises an alcohol gas or a nitrogen gas.

28. (New) The apparatus of claim 18, wherein the gas comprises an alcohol gas

or a nitrogen gas.

29. (New) The apparatus of claim 8, wherein the separation plate is moved along a first direction and each of the exhaust path is formed perpendicular to the first direction.

30. (New) The apparatus of claim 18, wherein the separation plate is moved along a first direction and the each of the exhaust path is formed perpendicular to the first direction.

31. (New) The apparatus of claim 20, wherein the separation plate is moved along a first direction and the each of the exhaust path is formed perpendicular to the first direction.